

IR-46

1. Color Infrared
2. Materials GaAs/GaAs
3. Electrode P(anode) side : Al
 N(cathode) side : Au
4. Electrode pattern Fig.1,2
5. Chip size 0.205mm X 0.205mm X 0.180mmH (Fig.1)
6. Emission area 0.185mm X 0.185mm (Fig.1)
7. Electro-Optical characteristics

Parameters	Symbol	Condition	Min	Typ	Max	Unit
Power	Po	IF=20mA	0.7	1.2	—	mW
Forward Voltage	VF	IF=20mA	—	1.25	1.50	V
Reverse Current	IR	VR=5V	—	—	10	uA
Peak Wavelength	* λp	IF=20mA	—	945	—	nm
Spectral Radiation Bandwidth	* Δλ	IF=20mA	—	40	—	nm

* 「*」 mark is reference data

* Power measurement at Resonac Photonics.

8. Recommended bonding method Ultra-sonic method or a combination of ultra-sonic and thermo-compression methods.

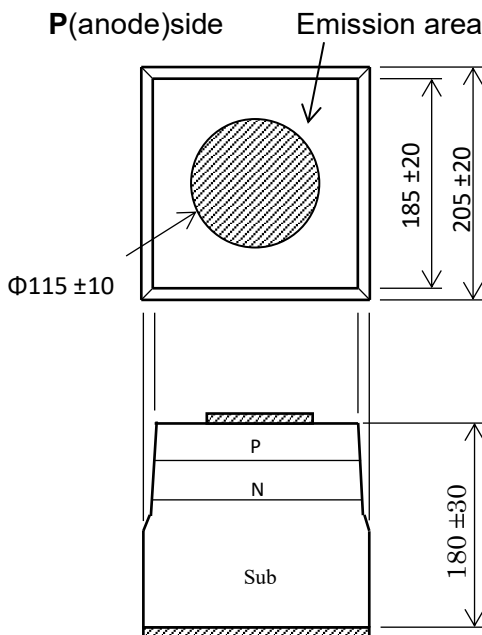


Fig.1 : Chip size and Emission area

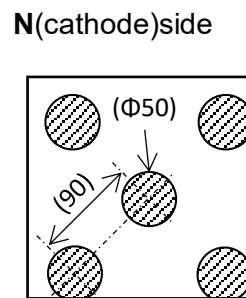


Fig.2 : Electrode pattern

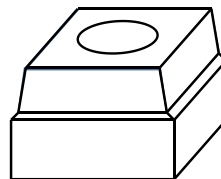


Fig.3 : No roughing

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